MSKSEMI















ESD

TVS

TSS

MOV

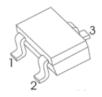
GDT

PLED

Brodnet data speet

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PNP Silicon Epitaxial Planar Transistor

1. BASE

2. EMITTER

3. COLLECTOR

SOT-323

for switching and amplifier applications

Absolute Maximum Ratings (T_a = 25 °C)

| Parameter | Symbol | Value | Unit |
|---------------------------|-------------------|--------------|------|
| Collector Base Voltage | -V _{CBO} | 40 | V |
| Collector Emitter Voltage | -V _{CEO} | 40 | V |
| Emitter Base Voltage | -V _{EBO} | 5 | V |
| Collector Current | -I _C | 200 | mA |
| Total Power Dissipation | P _{tot} | 200 | mW |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature Range | T _{stg} | - 55 to +150 | °C |

CLASSIFICATION OF her

| RANGE | 100-300 | |
|---------|---------|--|
| MARKING | 2A | |
| | | |



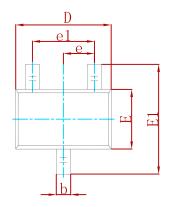
MMBT3906W HF €

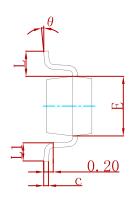


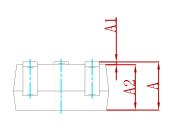
Characteristics at T_a = 25 °C

| Parameter | Symbol | Min. | Max. | Unit |
|--|--|-----------------------------|--------------------|------------------|
| DC Current Gain at $-V_{CE} = 1 \text{ V}$, $-I_{C} = 0.1 \text{ mA}$ at $-V_{CE} = 1 \text{ V}$, $-I_{C} = 1 \text{ mA}$ at $-V_{CE} = 1 \text{ V}$, $-I_{C} = 10 \text{ mA}$ at $-V_{CE} = 1 \text{ V}$, $-I_{C} = 50 \text{ mA}$ at $-V_{CE} = 1 \text{ V}$, $-I_{C} = 100 \text{ mA}$ | h _{FE} h _{FE} h _{FE} h _{FE} | 60 80 100 60 30 | - 300 - - | - - - - |
| Collector Emitter Cutoff Current at -V _{CE} = 30 V | -I _{CES} | - | 50 | nA |
| Emitter Base Cutoff Current at -V _{EB} = 3 V | -I _{EBO} | - | 50 | nA |
| Collector Base Breakdown Voltage at $-I_C = 10 \mu A$ | -V _{(BR)CBO} | 40 | - | V |
| Collector Emitter Breakdown Voltage at -I _C = 1 mA | -V _{(BR)CEO} | 40 | - | V |
| Emitter Base Breakdown Voltage at -I _E = 10 μA | -V _{(BR)EBO} | 5 | - | V |
| Collector Emitter Saturation Voltage at $-I_C = 10$ mA, $-I_B = 1$ mA at $-I_C = 50$ mA, $-I_B = 5$ mA | -V _{CE(sat)} | | 0.25 0.4 | V |
| Base Emitter Saturation Voltage at $-I_C = 10$ mA, $-I_B = 1$ mA at $-I_C = 50$ mA, $-I_B = 5$ mA | -V _{BE(sat)} | 0.65 - | 0.85 0.95 | V |
| Transition Frequency at $-V_{CE} = 20 \text{ V}$, $I_E = 10 \text{ mA}$, $f = 100 \text{ MHz}$ | f _⊤ | 250 | - | MHz |
| Collector Output Capacitance at $-V_{CB} = 10 \text{ V}$, f = 100 KHz | C _{ob} | - | 4.5 | pF |
| Delay Time at $-V_{CC} = 3 \text{ V}$, $-V_{BE(OFF)} = 0.5 \text{ V}$, $-I_C = 10 \text{ mA}$, $-I_{B1} = 1 \text{ mA}$ | t _d | - | 35 | ns |
| Rise Time at $-V_{CC} = 3 \text{ V}$, $-V_{BE(OFF)} = 0.5 \text{ V}$, $-I_C = 10 \text{ mA}$, $-I_{B1} = 1 \text{ mA}$ | t _r | - | 35 | ns |
| Storage Time at $-V_{CC} = 3 \text{ V}$, $-I_C = 10 \text{ mA}$, $I_{B1} = -I_{B2} = -1 \text{ mA}$ | t _{stg} | - | 225 | ns |
| Fall Time at $-V_{CC} = 3 \text{ V}$, $-I_{C} = 10 \text{ mA}$, $I_{B1} = -I_{B2} = -1 \text{ mA}$ | t _f | - | 75 | ns |

PACKAGE MECHANICAL DATA

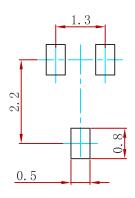






| Symbol Dimensi | | In Millimeters | Dimensions In Inches | |
|----------------|-------|----------------|----------------------|-------|
| Symbol | Min | Max | Min | Max |
| Α | 0.900 | 1.100 | 0.035 | 0.043 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.000 | 0.035 | 0.039 |
| b | 0.200 | 0.400 | 0.008 | 0.016 |
| С | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.000 | 2.200 | 0.079 | 0.087 |
| Е | 1.150 | 1.350 | 0.045 | 0.053 |
| E1 | 2.150 | 2.450 | 0.085 | 0.096 |
| е | 0.650 |) TYP | 0.026 | 6 TYP |
| e1 | 1.200 | 1.400 | 0.047 | 0.055 |
| L | 0.525 | REF | 0.021 | REF |
| L1 | 0.260 | 0.460 | 0.010 | 0.018 |
| θ | 0° | 8° | 0° | 8° |

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|-----------|---------|------|
| MMBT3906W | SOT-323 | 3000 |



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